



### **30V Complementary Enhancement Mode MOSFET**

Voltage

30 / -30V

Current

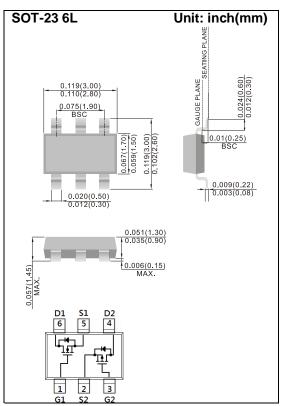
4.4 /-3.1A

#### **Features**

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

#### **Mechanical Data**

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	30	-30	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 12	<u>+</u> 12	V
Continuous Drain Current		I <sub>D</sub>	4.4	-3.1	Α
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	17.6	-12.4	А
B	T <sub>a</sub> =25°C	1	1.25		W
Power Dissipation	Derate above 25°C	P <sub>D</sub>	1	mW/°C	
Operating Junction and Storage Tem	$T_J, T_{STG}$	-55~150		°C	
Typical Thermal resistance					
- Junction to Ambient (Note 3)		$R_{\theta JA}$	100		100





# N-Channel Electrical Characteristics (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}$ =0V, $I_D$ =250uA	30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.4	0.72	1.2	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =4.4A	-	37	48	mΩ	
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.6A	-	40	53		
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.5A	-	48	66		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =30V, $V_{GS}$ =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 5)							
Total Gate Charge	$Q_g$	\/ 45\/   440	-	11.3	-	nC	
Gate-Source Charge	$Q_gs$	$V_{DS}$ =15V, $I_{D}$ =4.4A, $V_{GS}$ =10V (Note 1,2)	-	1	-		
Gate-Drain Charge	$Q_gd$		-	1.2	-		
Input Capacitance	Ciss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	447	-	pF	
Output Capacitance	Coss		-	34	-		
Reverse Transfer Capacitance	Crss		-	22	-		
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =15V, $I_{D}$ =4.4A, $V_{GS}$ =10V, $R_{G}$ =3 $\Omega$ (Note 1,2)	-	1.7	-		
Turn-On Rise Time	tr		-	38	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>		-	82	-		
Turn-Off Fall Time	tf		-	64	-		
Drain-Source Diode							
Maximum Continuous Drain-Source					1 5	A	
Diode Forward Current	Is		_	-	1.5	A	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.77	1.2	V	

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing





### **P-Channel Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-0.5	-0.96	-1.3	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3.1A	-	82	98	mΩ	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2.2A	-	91	114		
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1.1A	-	115	165		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-30V, $V_{GS}$ =0V	-	-	-1	uA	
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 5)							
Total Gate Charge	$Q_g$	\/ 45\/   244	-	11	-	nC	
Gate-Source Charge	$Q_gs$	V <sub>DS</sub> =-15V, I <sub>D</sub> =-3.1A, V <sub>GS</sub> =-10V <sup>(Note 1,2)</sup>	-	0.85	-		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =-10V	-	1.4	-		
Input Capacitance	Ciss	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	443	-	pF	
Output Capacitance	Coss		-	38	-		
Reverse Transfer Capacitance	Crss		-	25	-		
Turn-On Delay Time	td <sub>(on)</sub>	\/ 45\/   24A	-	2.5	-		
Turn-On Rise Time	tr	$V_{DD}$ =-15V, $I_{D}$ =-3.1A, $V_{GS}$ =-10V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	32	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>		-	161	-		
Turn-Off Fall Time	tf		-	73	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	,				-1.5	Α	
Diode Forward Current	I <sub>S</sub>		is	-	-	-1.5	A
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	-0.79	-1.2	V	

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
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#### N-Channel TYPICAL CHARACTERISTIC CURVES

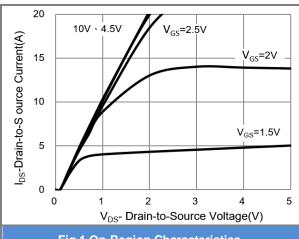


Fig.1 On-Region Characteristics

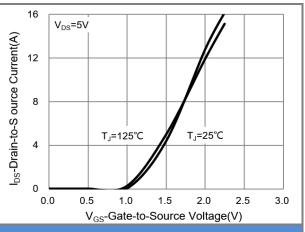


Fig.2 Transfer Characteristics

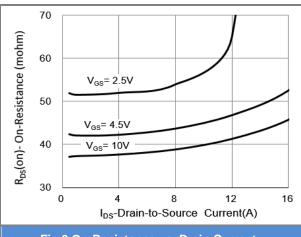


Fig.3 On-Resistance vs. Drain Current

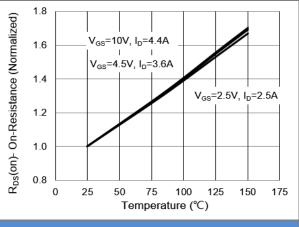


Fig.4 On-Resistance vs. Junction temperature

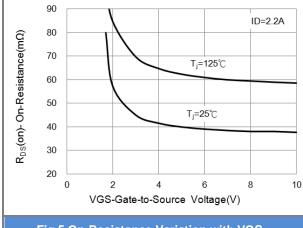
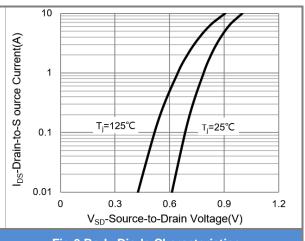


Fig.5 On-Resistance Variation with VGS.



**Fig.6 Body Diode Characteristics** 





### N-Channel TYPICAL CHARACTERISTIC CURVES

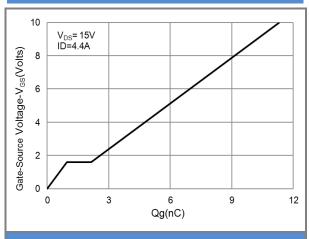


Fig.7 Gate-Charge Characteristics

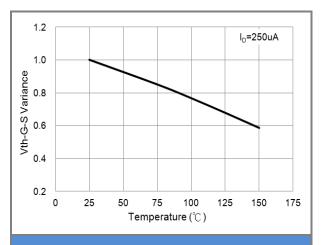


Fig.8 Threshold Voltage Variation with Temperature.

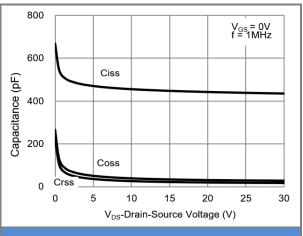


Fig.9 Capacitance vs. Drain-Source Voltage.





#### P-Channel TYPICAL CHARACTERISTIC CURVES

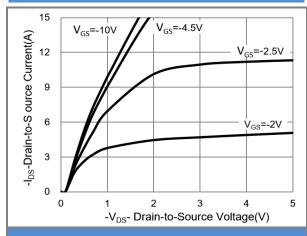
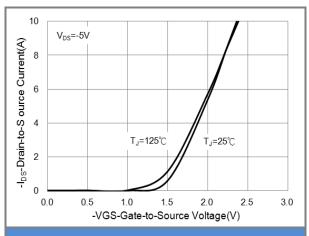


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

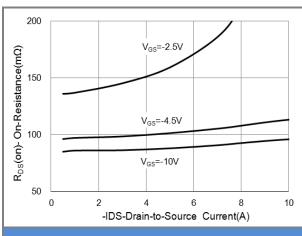


Fig.3 On-Resistance vs. Drain Current

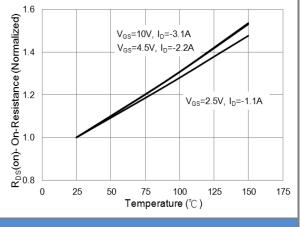
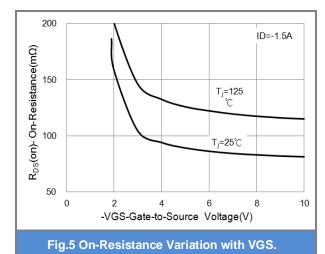
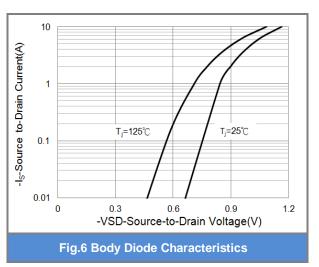


Fig.4 On-Resistance vs. Junction temperature









### P-Channel TYPICAL CHARACTERISTIC CURVES

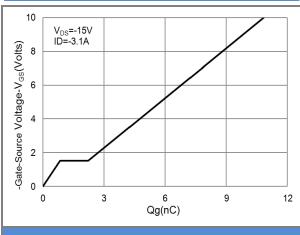


Fig.7 Gate-Charge Characteristics

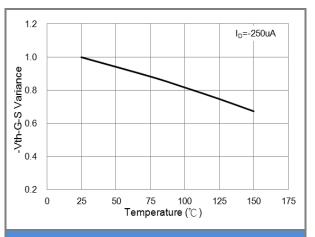
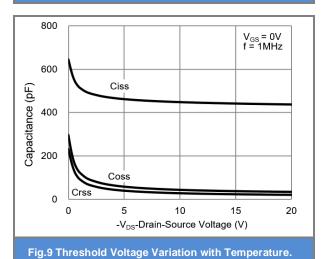


Fig.8 Threshold Voltage Variation with Temperature.



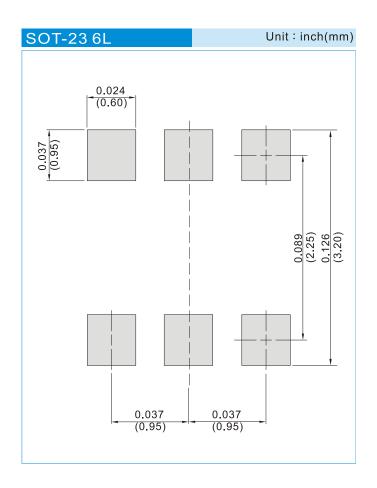




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJS6604_S1_00001	SOT-23 6L	3K pcs / 7" reel	SC4	Halogen free
PJS6604_S2_00001	SOT-23 6L	10K pcs / 13" reel	SC4	Halogen free

### **MOUNTING PAD LAYOUT**







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